

SN54AC00-SP 抗辐射加固型四路 2 输入与非门

1 特性

- 5962R87549 :
 - 抗辐射加固保障 (RHA) 高达 100 krad (Si) 总电离剂量 (TID)
 - SEL 抗扰度为 86 MeV×cm²/mg
- 5962-87549 :
 - 总电离剂量为 50 krad (Si)
- 2 V 至 6 V V_{CC} 运行
- 输入电压高达 6 V
- 5V 时 t_{pd} 最大值为 7 ns

2 应用

- 卫星有效载荷
- 卫星上电复位逻辑
- 适用于太空混合动力车的 RHA 已知合格芯片 (KGD) 产品

引脚功能 (每个逻辑门)

| 输入 | | 输出 Y |
|----|---|---------|
| A | B | |
| H | H | L |
| L | X | H |
| X | L | H |



逻辑图 (正逻辑)

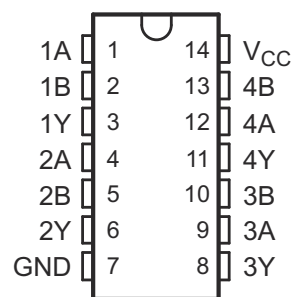
3 说明

SN54AC00 器件包含四个独立双输入与非门。每个逻辑门以正逻辑执行布尔函数 $Y = \overline{A \cdot B}$ 或 $Y = \overline{A + B}$ 。

器件信息⁽¹⁾

| 器件型号 | 封装 | 封装尺寸 (标称值) |
|-------------|-----------|--------------------|
| SN54AC00-SP | CDIP (14) | 5.97 mm × 9.21 mm |
| | CFP (14) | 6.67 mm × 19.56 mm |
| | KGD (0) | 不可用 |

(1) 如需了解所有可用封装, 请参阅数据表末尾的可订购产品附录。



J 或 W 封装
(顶视图)



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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

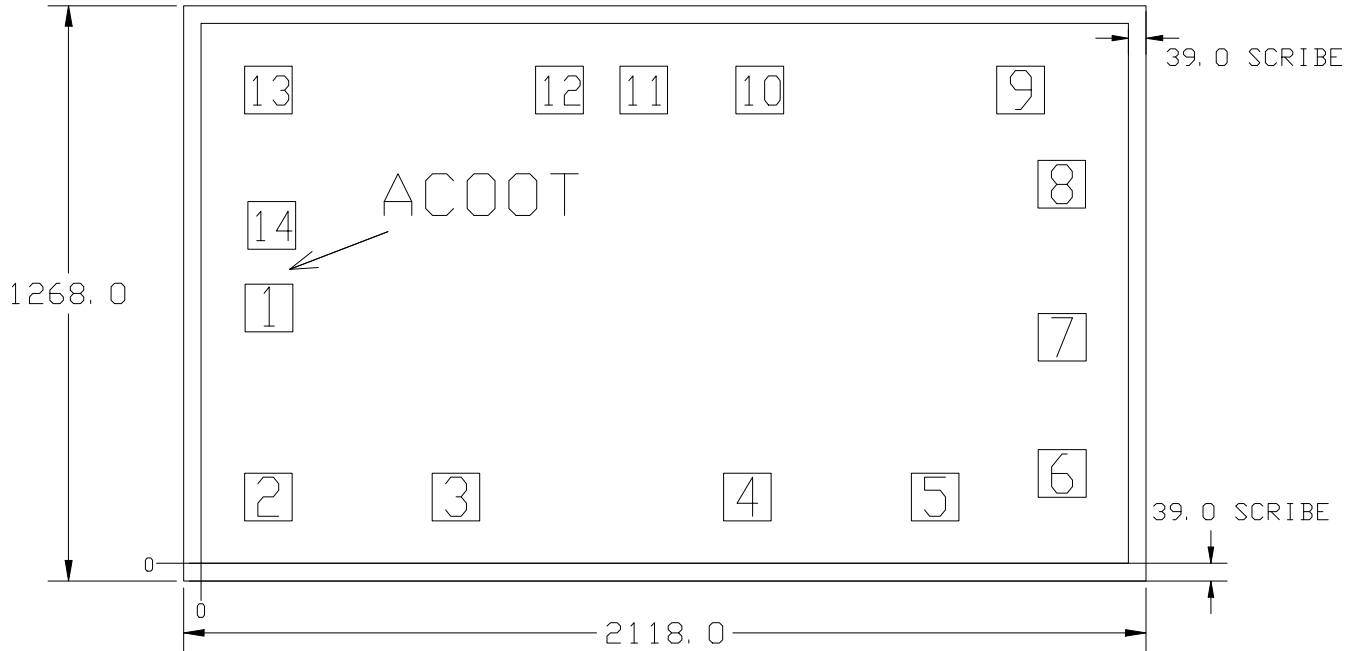
| Changes from Revision B (October 2015) to Revision C (April 2022) | Page |
|--|-------------|
| • 更新了整个文档中的表格、图和交叉参考的编号格式..... | 1 |
| • 删除了 <i>特性</i> 部分中的 <i>SEU</i> | 1 |
| • 将 <i>SEL</i> 抗扰度更改为 $86\text{ MeV}\times\text{cm}^2/\text{mg}$ | 1 |

| Changes from Revision A (December 2013) to Revision B (February 2015) | Page |
|--|-------------|
| • 添加了 KGD 封装信息..... | 1 |
| • 添加了 <i>器件和文档支持</i> 部分以及 <i>机械、封装和可订购信息</i> 部分..... | 1 |
| • Added <i>Bare Die Information</i> , image, and <i>Bond Pad Coordinates in Microns</i> | 3 |
| • Added parameter information for KGD to 节 6.5 and 节 6.6 | 6 |

| Changes from Revision * (October 2008) to Revision A (December 2013) | Page |
|---|-------------|
| • 更改了 <i>特性</i> 列表项..... | 1 |
| • 删除了 <i>订购信息表</i> | 1 |

5 Bare Die Information

| DIE THICKNESS | BACKSIDE FINISH | BACKSIDE POTENTIAL | BOND PAD METALLIZATION COMPOSITION | BOND PAD THICKNESS |
|---------------|------------------------|--------------------|------------------------------------|--------------------|
| 15 mils | Silicon with backgrind | Floating | TiW/AlCu2 | 15800 nm |



Bond Pad Coordinates in Microns

| DESCRIPTION | PAD NUMBER | X MIN | Y MIN | X MAX | Y MAX |
|-------------|------------|--------|-------|--------|-------|
| 1A | 1 | 96.3 | 510.5 | 201.3 | 615.5 |
| 1B | 2 | 95 | 94 | 200 | 199 |
| 1Y | 3 | 508 | 94 | 613 | 199 |
| 2A | 4 | 1149 | 94 | 1254 | 199 |
| 2B | 5 | 1562 | 94 | 1667 | 199 |
| 2Y | 6 | 1841.5 | 145.5 | 1946.5 | 250.5 |
| GND | 7 | 1841.5 | 445.5 | 1946.5 | 550.5 |
| 3Y | 8 | 1841 | 783 | 1946 | 888 |
| 3A | 9 | 1750.5 | 991 | 1855.5 | 1096 |
| 3B | 10 | 1176.5 | 991 | 1281.5 | 1096 |
| 4Y | 11 | 921 | 991 | 1026 | 1096 |
| 4A | 12 | 736 | 991 | 841 | 1096 |
| 4B | 13 | 95 | 991 | 200 | 1096 |
| VCC | 14 | 102.5 | 692 | 207.5 | 797 |

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

| | | MIN | MAX | UNIT | |
|------------------|---|--|-----------------------|------|----|
| V _{CC} | Supply voltage | - 0.5 | 7 | V | |
| V _I | Input voltage ⁽²⁾ | - 0.5 | V _{CC} + 0.5 | V | |
| V _O | Output voltage ⁽²⁾ | - 0.5 | V _{CC} + 0.5 | V | |
| I _{IK} | Input clamp current | V _I < 0 or V _I > V _{CC} | | ±20 | mA |
| I _{OK} | Output clamp current | V _O < 0 or V _O > V _{CC} | | ±20 | mA |
| I _O | Continuous output current | V _O = 0 to V _{CC} | | ±50 | mA |
| | Continuous current through V _{CC} or GND | | | ±200 | mA |
| T _J | Junction temperature | | | 150 | °C |
| T _{stg} | Storage temperature | - 65 | 150 | °C | |

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

6.2 Recommended Operating Conditions

| | | MIN | MAX | UNIT | |
|-----------------|------------------------------------|-------------------------|-----------------|------|------|
| V _{CC} | Supply voltage | 2 | 6 | V | |
| V _{IH} | High-level input voltage | V _{CC} = 3 V | 2.1 | V | |
| | | V _{CC} = 4.5 V | 3.15 | | |
| | | V _{CC} = 5.5 V | 3.85 | | |
| V _{IL} | Low-level input voltage | V _{CC} = 3 V | 0.9 | V | |
| | | V _{CC} = 4.5 V | 1.35 | | |
| | | V _{CC} = 5.5 V | 1.65 | | |
| V _I | Input voltage | 0 | V _{CC} | V | |
| V _O | Output voltage | 0 | V _{CC} | V | |
| I _{OH} | High-level output current | V _{CC} = 3 V | 12 | mA | |
| | | V _{CC} = 4.5 V | 24 | | |
| | | V _{CC} = 5.5 V | 24 | | |
| I _{OL} | Low-level output current | V _{CC} = 3 V | 12 | mA | |
| | | V _{CC} = 4.5 V | 24 | | |
| | | V _{CC} = 5.5 V | 24 | | |
| Δt/Δv | Input transition rise or fall rate | | | 8 | ns/V |
| T _A | Operating free-air temperature | - 55 | 125 | °C | |

6.3 Thermal Information

| THERMAL METRIC ^{(1) (2)} | | SN54AC00-SP | | UNIT |
|-----------------------------------|--|-------------|---------|------|
| | | J | W | |
| | | 14 PINS | 14 PINS | |
| $R_{\theta JA}$ | Junction-to-ambient thermal resistance | 83.1 | 125.4 | °C/W |
| $R_{\theta JC(top)}$ | Junction-to-case (top) thermal resistance | 26.6 | 30.85 | |
| $R_{\theta JB}$ | Junction-to-board thermal resistance | 47.9 | 43.4 | |
| ψ_{JT} | Junction-to-top characterization parameter | N/A | N/A | |
| ψ_{JB} | Junction-to-board characterization parameter | N/A | N/A | |
| $R_{\theta JC(bot)}$ | Junction-to-case (bottom) thermal resistance | N/A | N/A | |

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).
(2) The package thermal impedance is calculated in accordance with JESD 51-7 and Mil Std 883 method 1012.1 (see [www.JEDEC.org](#)).

6.4 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | V_{CC} | $T_A = 25^\circ\text{C}$ | | | MIN | MAX | UNIT |
|---------------------------------|----------------------------------|----------|--------------------------|-----|------|-----------|---------|---------------|
| | | | MIN | TYP | MAX | | | |
| V_{OH} | $I_{OH} = -50 \mu\text{A}$ | 3 V | 2.9 | | | 2.9 | | V |
| | | 4.5 V | 4.4 | | | 4.4 | | |
| | | 5.5 V | 5.4 | | | 5.4 | | |
| | $I_{OH} = -12 \text{ mA}$ | 3 V | 2.56 | | | 2.4 | | |
| | | 4.5 V | 3.86 | | | 3.7 | | |
| | | 5.5 V | 4.86 | | | 4.7 | | |
| $I_{OH} = -50 \text{ mA}^{(1)}$ | 5.5 V | | | | 3.85 | | | |
| V_{OL} | $I_{OL} = 50 \mu\text{A}$ | 3 V | | | | 0.1 | 0.1 | V |
| | | 4.5 V | | | | 0.1 | 0.1 | |
| | | 5.5 V | | | | 0.1 | 0.1 | |
| | $I_{OL} = 12 \text{ mA}$ | 3 V | | | | 0.36 | 0.5 | |
| | | 4.5 V | | | | 0.36 | 0.5 | |
| | | 5.5 V | | | | 0.36 | 0.5 | |
| $I_{OL} = 50 \text{ mA}^{(1)}$ | 5.5 V | | | | | 1.65 | | |
| I_I | $V_I = V_{CC}$ or GND | 5.5 V | | | | ± 0.1 | ± 1 | μA |
| I_{CC} | $V_I = V_{CC}$ or GND, $I_O = 0$ | 5.5 V | | | | 4 | 40 | μA |
| C_i | $V_I = V_{CC}$ or GND | 5 V | 2.6 | | | | | pF |

- (1) Not more than one output should be tested at a time, and the duration of the test should not exceed 2 ms.

6.5 Switching Characteristics, $V_{CC} = 3.3\text{ V}$

over recommended operating free-air temperature range, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$ (unless otherwise noted) (see [Figure 7-1](#))

| PARAMETER | FROM (INPUT) | TO (OUTPUT) | $T_A = 25^\circ\text{C}$ | | | MIN | MAX | UNIT |
|-------------------------------------|-----------------|----------------|--------------------------|-----|-----|-----|-----|------|
| | | | MIN | TYP | MAX | | | |
| t_{PLH} | A or B | Y | 2 | 7 | 9.5 | 1 | 11 | ns |
| t_{PHL} | | | 1.5 | 5.5 | 8 | 1 | 9 | |
| t_{PLH} (KGD only) ⁽¹⁾ | A or B | Y | 1 | 7 | 9.5 | 1 | 11 | ns |
| t_{PHL} (KGD only) ⁽¹⁾ | | | 1 | 5.5 | 9.5 | 1 | 11 | |

(1) Specification limits for KGD are based on SMD 5962-8754903

6.6 Switching Characteristics, $V_{CC} = 5\text{ V}$

over recommended operating free-air temperature range, $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$ (unless otherwise noted) (see [Figure 7-1](#))

| PARAMETER | FROM (INPUT) | TO (OUTPUT) | $T_A = 25^\circ\text{C}$ | | | MIN | MAX | UNIT |
|-------------------------------------|-----------------|----------------|--------------------------|-----|-----|-----|-----|------|
| | | | MIN | TYP | MAX | | | |
| t_{PLH} | A or B | Y | 1.5 | 6 | 8 | 1 | 8.5 | ns |
| t_{PHL} | | | 1.5 | 4.5 | 6.5 | 1 | 7 | |
| t_{PLH} (KGD only) ⁽¹⁾ | A or B | Y | 1.5 | 6 | 8 | 1 | 8.5 | ns |
| t_{PHL} (KGD only) ⁽¹⁾ | | | 1.5 | 4.5 | 8 | 1 | 8.5 | |

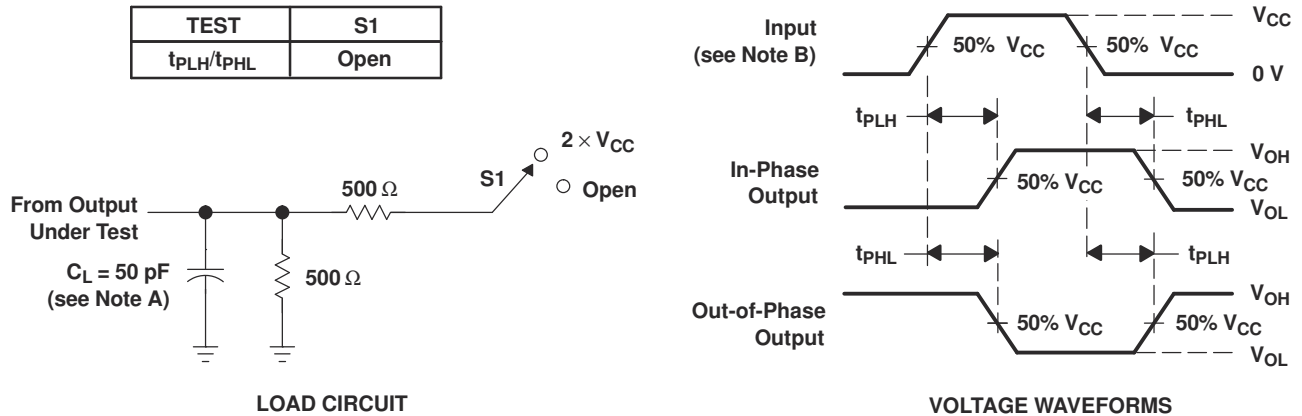
(1) Specification limits for KGD are based on SMD 5962-8754903

6.7 Operating Characteristics

$V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

| PARAMETER | TEST CONDITIONS | TYP | UNIT |
|--|---|-----|------|
| C_{pd} Power dissipation capacitance | $C_L = 50\text{ pF}$, $f = 1\text{ MHz}$ | 40 | pF |

7 Parameter Measurement Information



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1\ \text{MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2.5\ \text{ns}$, $t_f \leq 2.5\ \text{ns}$.
 - C. The outputs are measured one at a time with one input transition per measurement.

图 7-1. Load Circuit and Voltage Waveforms

8 Device and Documentation Support

8.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

8.2 支持资源

TI E2E™ [支持论坛](#) 是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《[使用条款](#)》。

8.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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8.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.5 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

TUBE


*All dimensions are nominal

| Device | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (μm) | B (mm) |
|-----------------|--------------|--------------|------|-----|--------|--------|--------|--------|
| 5962-8754903VDA | W | CFP | 14 | 25 | 506.98 | 26.16 | 6220 | NA |
| 5962R8754903VCA | J | CDIP | 14 | 25 | 506.98 | 15.24 | 13440 | NA |
| 5962R8754903VDA | W | CFP | 14 | 25 | 506.98 | 26.16 | 6220 | NA |

W (R-GDFP-F14)

CERAMIC DUAL FLATPACK



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. This package can be hermetically sealed with a ceramic lid using glass frit.
 - D. Index point is provided on cap for terminal identification only.
 - E. Falls within MIL STD 1835 GDFP1-F14

J 14

GENERIC PACKAGE VIEW
CDIP - 5.08 mm max height
CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4040083-5/G

J0014A



PACKAGE OUTLINE

CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



4214771/A 05/2017

NOTES:

1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This package is hermetically sealed with a ceramic lid using glass frit.
4. Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
5. Falls within MIL-STD-1835 and GDIP1-T14.

EXAMPLE BOARD LAYOUT

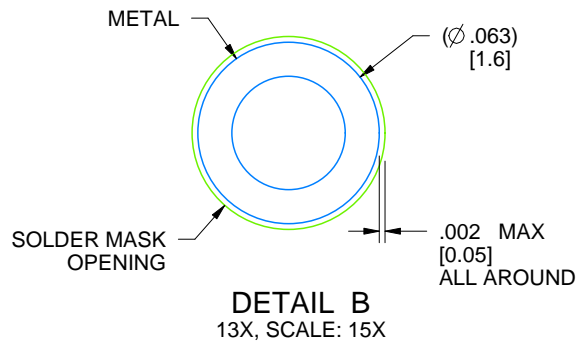
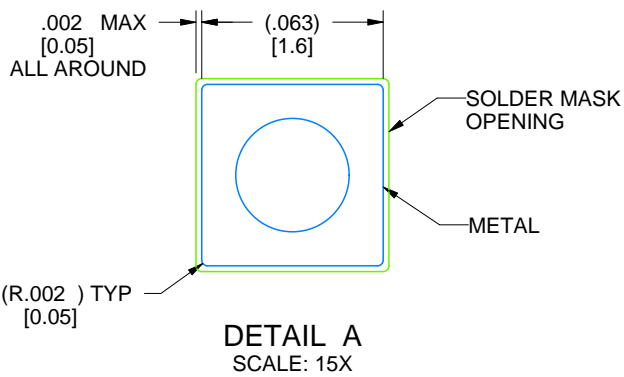
J0014A

CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



LAND PATTERN EXAMPLE
NON-SOLDER MASK DEFINED
SCALE: 5X



4214771/A 05/2017

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